



Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _C = +25°C (Note 9)
60V	5.5mΩ @ V _{GS} = 10V	100A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- High Frequency Switching
- Sync. Rectification
- DCDC Converters

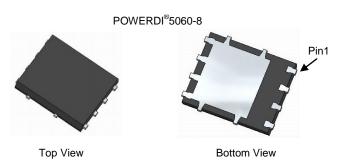
60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI[®]

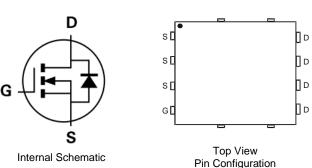
Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low R_{DS(ON)} minimizes power losses
- Low Q_g minimizes switching losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMTH6005LPSQ</u>)

Mechanical Data

- Case: POWERDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)





Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH6005LPS-13	POWERDI [®] 5060-8	2,500 / Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



) | | = Manufacturer's Marking H6005LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 15 = 2015) WW = Week (01 - 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage		V _{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V	
Continuous Drain Current (Note 5)	T _A = +25°C T _A = +70°C	ID	20.6 17.2	A	
Continuous Drain Current (Note 6)	T _C = +25°C (Note 9)	Ι _D	100	А	
	$T_{C} = +100^{\circ}C$		90		
Maximum Continuous Body Diode Forward Current (Note 6)		Is	100	A	
Pulsed Drain Current (10μs pulse, duty cycle = 1%)		I _{DM}	160	A	
Avalanche Current, L=1mH		I _{AS}	14.8	A	
Avalanche Energy, L=1mH		E _{AS}	98	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	PD	3.2	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	47	°C/W	
Total Power Dissipation (Note 6)	T _C = +25°C	PD	150	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

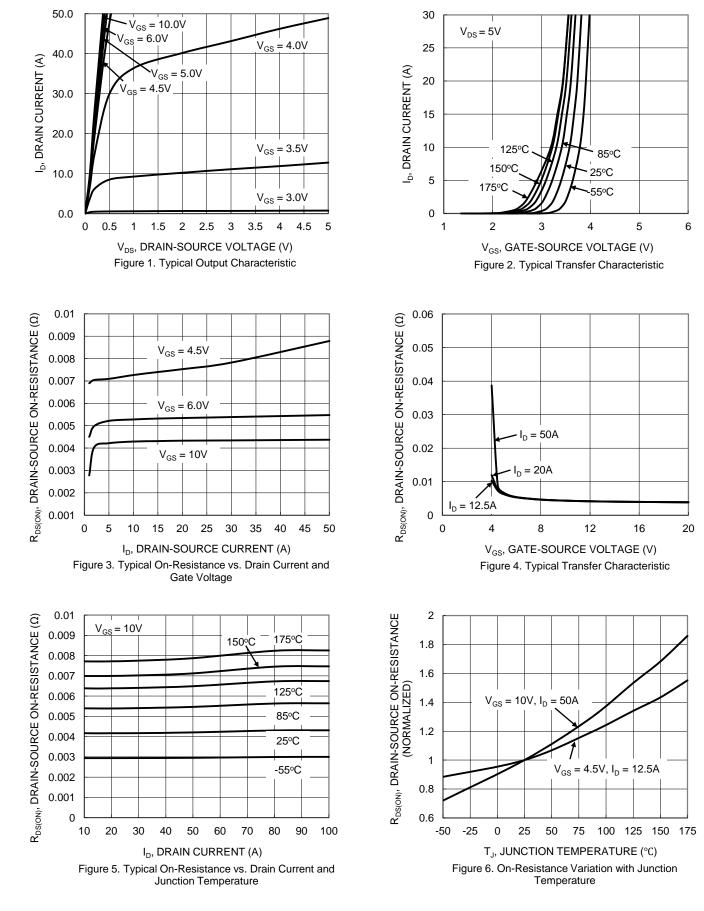
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	• •			•			
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
		-	4.4	5.5	mΩ	$V_{GS} = 10V, I_D = 50A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	5.7	7.2		$V_{GS} = 6V, I_D = 20A$	
		-	7.7	10		V _{GS} = 4.5V, I _D = 12.5A	
Diode Forward Voltage	V _{SD}	-	0.9	-	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 8)	• •			•			
Input Capacitance	C _{iss}	-	2962	-			
Output Capacitance	Coss	-	965.2	-	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	Crss	-	59.8	-			
Gate Resistance	Rq	-	0.66	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qq	-	47.1	-			
Total Gate Charge (V _{GS} = 4.5V)	Qq	-	23.1	-	-0		
Gate-Source Charge	Q _{qs}	-	10.2	-	nC	$V_{DD} = 30V, I_D = 50A$	
Gate-Drain Charge	Q _{gd}	-	12.5	-			
Turn-On Delay Time	t _{D(ON)}	-	8.3	-		$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-On Rise Time	t _R	-	9.4	-			
Turn-Off Delay Time	t _{D(OFF)}	-	22	-	ns	$I_{\rm D} = 30$ A, $R_{\rm G} = 3.3\Omega$	
Turn-Off Fall Time	tF	-	8.9	-			
Body Diode Reverse Recovery Time	t _{RR}	-	40.4	-	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	-	49.7	-	nC	I _F = 30A, di/dt = 100A/µs	

Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.
Package limited.

Notes:



DMTH6005LPS



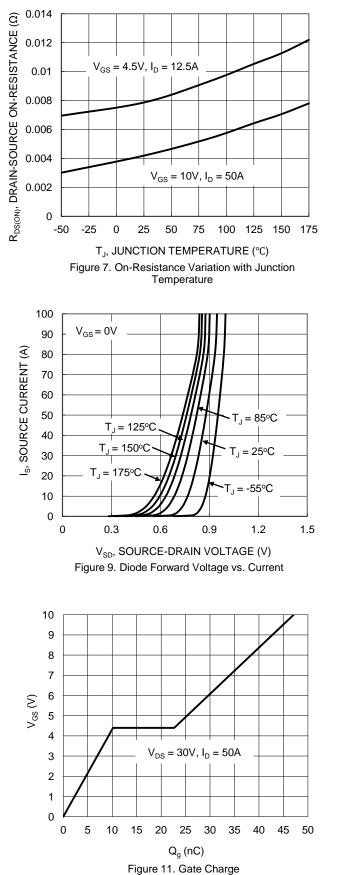
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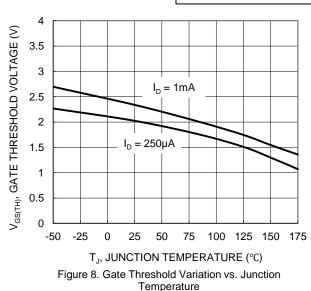
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NEW PRODUCT



DMTH6005LPS





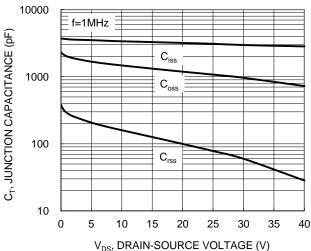


Figure 10. Typical Junction Capacitance

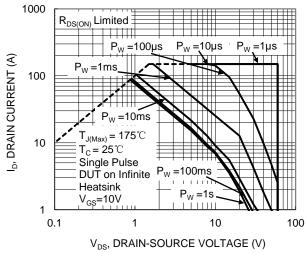
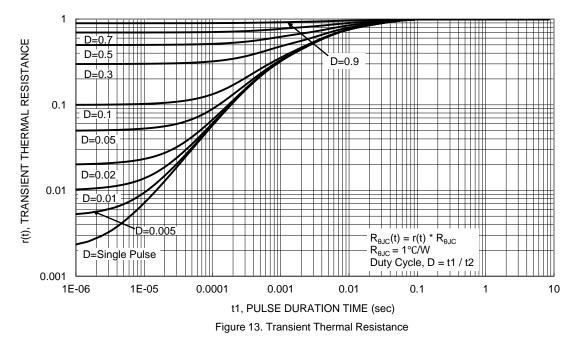


Figure 12. SOA, Safe Operation Area



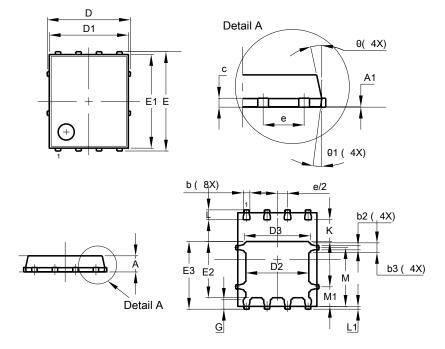




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

POWERDI[®]5060-8

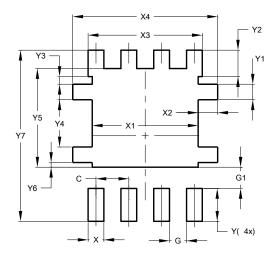


	POWERDI [®] 5060-8					
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05	-			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D		5.15 BSC				
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90	4.30	4.10			
Е	(6.15 BSC	;			
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е	1.27 BSC					
G	0.51	0.71	0.61			
K	0.51	-	-			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
θ	10º	12º	11º			
θ1	6º	8º	7º			
All	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

POWERDI[®]5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
X3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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